

isc Silicon NPN Power Transistor

2SC3894

DESCRIPTION

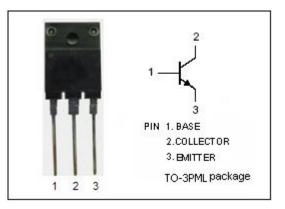
- High Breakdown Voltage-
- : V_{(BR)CBO}= 1500V(Min)
- High Switching Speed
- High Reliability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

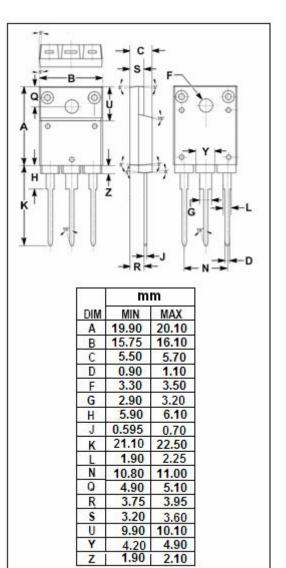
APPLICATIONS

Ultrahigh-definition CRT display horizontal deflection output applications

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)							
PARAMETER	VALUE	UNIT					
Collector-Base Voltage	1500	V					
Collector-Emitter Voltage	800	V					
Emitter-Base Voltage	6	V					
Collector Current-Continuous	6	А					
Collector Current-Peak	16	A					
Collector Power Dissipation @ $T_a=25^{\circ}C$	3.0						
Collector Power Dissipation @ $T_c=25^{\circ}C$	60	W					
Junction Temperature	150	°C					
tg Storage Temperature Range		°C					
	PARAMETERCollector-Base VoltageCollector-Emitter VoltageEmitter-Base VoltageCollector Current-ContinuousCollector Current-PeakCollector Power Dissipation @ $T_a=25^{\circ}C$ Collector Power Dissipation @ $T_c=25^{\circ}C$ Junction Temperature	PARAMETERVALUECollector-Base Voltage1500Collector-Emitter Voltage800Emitter-Base Voltage6Collector Current-Continuous6Collector Current-Peak16Collector Power Dissipation @ Ta=25°C3.0Collector Power Dissipation @ Tc=25°C60Junction Temperature150					

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)





isc website: www.iscsemi.com



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ELECTRICAL CHARACTERISTICS

$T_{c}\text{=}25^{\circ}\!\!\!\!\mathrm{C}$ unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 10mA; I _B = 0	800			v
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 4A; I _B = 1A			5.0	v
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 4A; I _B = 1A			1.5	v
Ісво	Collector Cutoff Current	V _{CB} = 800V; I _E = 0			10	μ Α
ICES	Collector Cutoff Current	V _{CE} = 1500V; R _{BE} = 0			1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V; I _C = 0			1.0	mA
h _{FE-1}	DC current gain	I _C = 1A; V _{CE} = 5V	8			
h _{FE-2}	DC current gain	Ic= 4A; Vc= 5V	4		8	
Switching ti	mes	1	1	1	1	1
t _{stg}	Storage Time	I _C = 4A , I _{B1} = 0.8A; I _{B2} = -1.6A R _L = 50 Ω ; V _{CC} = 200V			3.0	μ S
t _f	Fall Time				0.2	μ S

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